PECVD1 SIOxNy ~3300A Recipe			PECVD1 SION 3000A Typical Film Properties
1. Chamber Clean (wet clean)	**2. Chamber (clean+coat)**	**3.LS SION Deposition**	**Calibrated every 2-4 weeks**
WET CLEAN	**STAMB_17**	**STAMB_18**	**Check for the latest update on UCSB Nanofab WIKI**
Wipe clean upper chamber walls with DI	step1: Initial t=10", p=2x10-2 T=250C	step1: Initial t=10"	
Wipe off upper chamber walls with IPA	step2: N2 purge t=30" p=300mT	step2: N2 purge t=30"	
	step3: evacuate, base pressure=2x10-2, t=10"	step3: evacuate, t=10"	
	step4:loop	step4:loop	
	step5:gass stabilization, t=30"	step5: SiON gass stabilization, t=30"	**SiON-3000A Typical Film properties**
	step6:etch chamber, t=30'	**step6:SiON deposition**	**Deposition rate~14.7nm/min**
	step7:evacuate, t=10"	**Time=22'**	**Refractive index@632.8nm=1.718**
	step8:N2 purge	**Temperature=250°C**	**Stress=135MPa**
	step9:evacuate	**Pressure=900mT**	**HF etch rate=420nm/min**
	step10:loop	**Gass Flow:**	**Particle count (min=70, max=740)**
	step11:SiON gass stabilization	**SiH4=150sccm**	**Mostly small size particles (0.160-0.213)um**
t~81.37sec➔	**step12:SiON deposition(200A coat) , t=1"53.6"**	**N2O= 17sccm**	**Uniformity within the wafer (98.0-99.3)%**
	step13:evacuate	**N2=125sccm**	
	step14:N2purge, t=30"	**NH3=1.53**	
	step15:end	**Power:**	
		RF1=22W	
		step7:evacuate, t=10"	
		step8:N2 purge t=30"	
		step9:evacuate t=10"	
		step10:loop